

## **MR27V3252D**

2,097,152-Word x 16-Bit or 4,194,304-Word x 8-Bit

8-Word x 16-Bit or 16-Word x 8-Bit Page Mode

Production Programmed Read Only Memory (P2ROM)

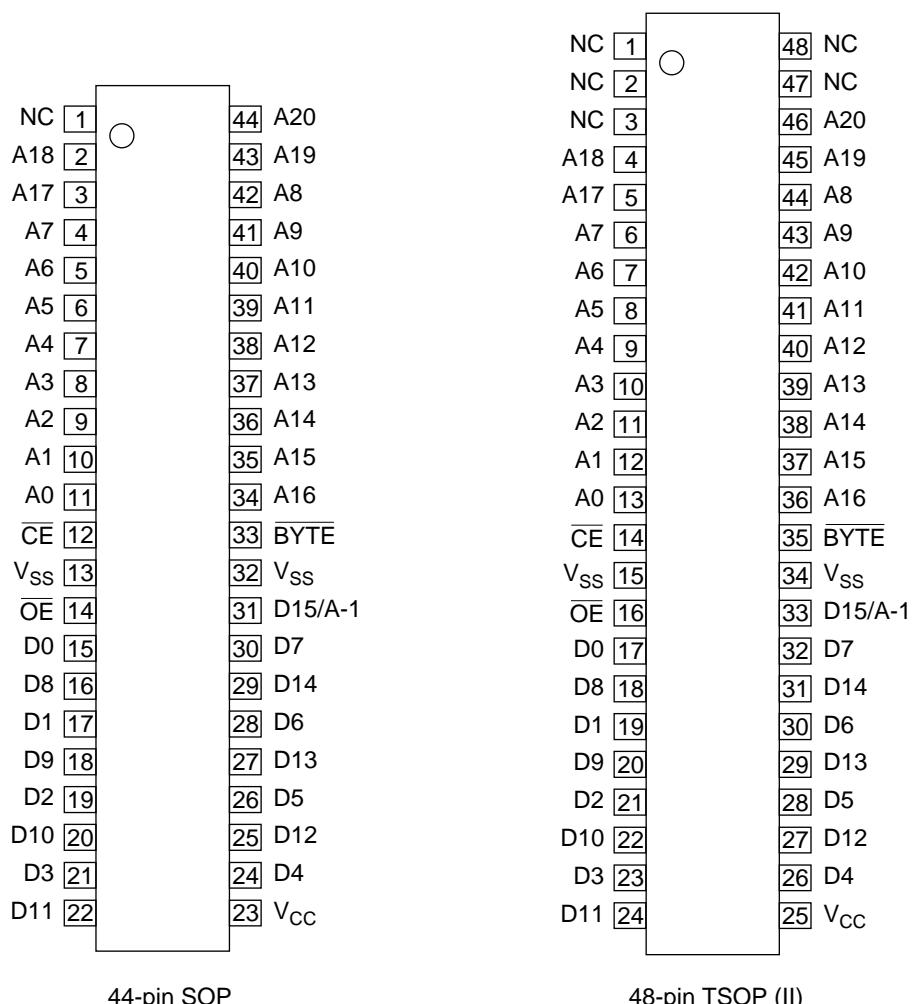
### **DESCRIPTION**

The MR27V3252D is a 32Mbit Production Programmed Read-Only Memory (P2ROM) with page mode. Its configuration can be electrically switched between 2,097,152 word x 16bit and 4,194,304 word x 8bit. The MR27V3252D operates on a single +3.3V power supply and is TTL compatible. The MR27V3252D provides Page mode which can greatly reduce the read access time. Since the MR27V3252D operates asynchronously, external clocks are not required, making this device easy-to-use. The MR27V3252D is suitable as large-capacity fixed memory for microcomputers and data terminals. It is manufactured using a CMOS double silicon gate technology and is offered in 44-pin SOP or 48-pin TSOP packages.

### **FEATURES**

- 2,097,152 word x 16bit / 4,194,304 word x 8bit electrically switchable configuration
- Single +3.3V power supply
- Access time 100ns
  - Page mode access time 30ns
- Input / Output TTL compatible
- Three-state output
- Packages
  - 44-pin plastic SOP (SOP44-P-600-1.27-K) (Product name : MR27V3252D-xxMA)
  - 48-pin plastic TSOP (TSOP II 48-P-550-0.80-K) (Product name : MR27V3252D-xxTA)

## PIN CONFIGURATION (TOP VIEW)

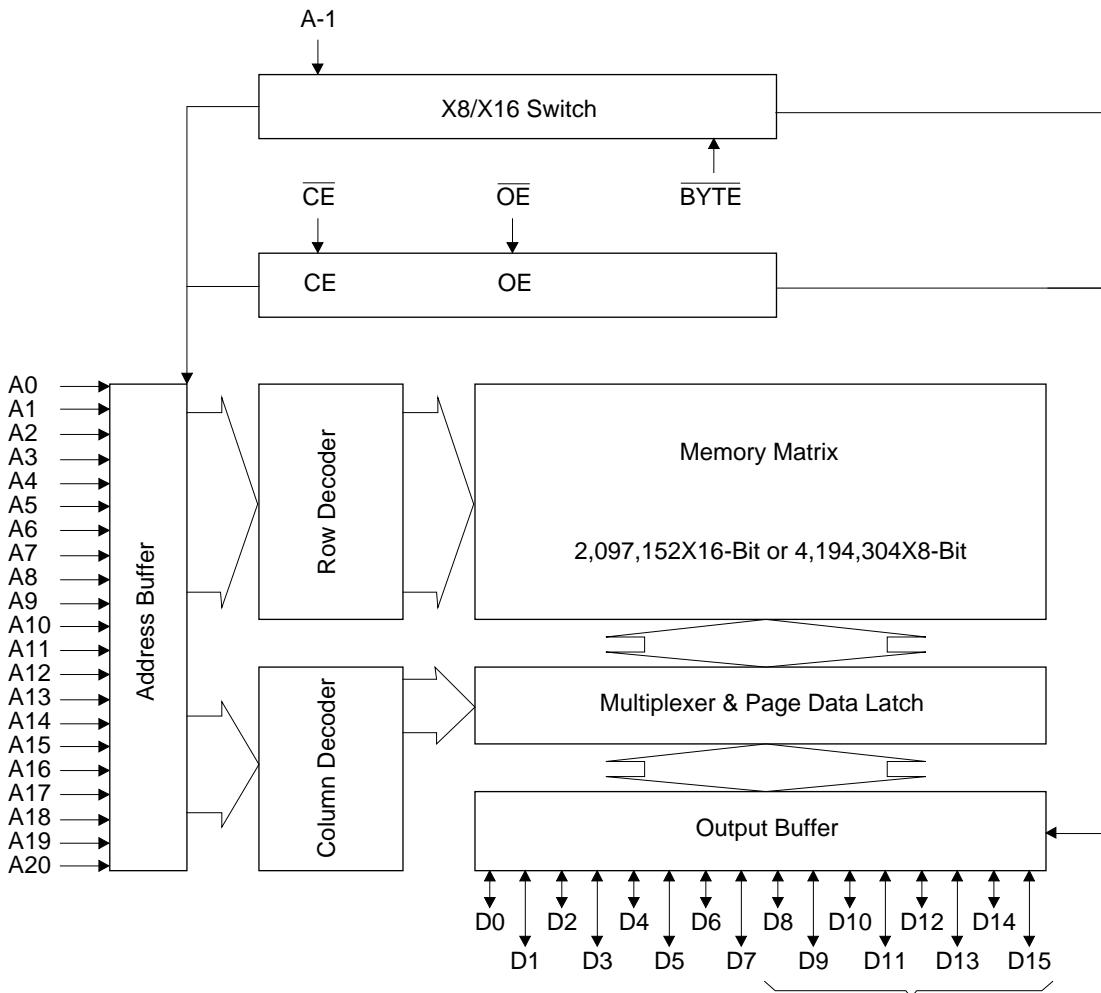


44-pin SOP

48-pin TSOP (II)

PIN NAMES	FUNCTIONS
D15/A-1	Data output / Address input
A0 - A20	Address input
D0 - D14	Data output
CE	Chip enable
OE	Output enable
V <sub>CC</sub>	Power supply voltage
V <sub>SS</sub>	GND
BYTE	Mode switch
NC	Non connection

## BLOCK DIAGRAM



In 8-bit output mode, these pins are three-stated and pin D15 functions as the A-1 address pin.

## FUNCTION TABLE

MODE	CE	OE	BYTE	V <sub>CC</sub>	D0 - D7	D8 - D14	D15/A-1
READ (16-Bit)	L	L	H	3.3V	D <sub>OUT</sub>		
READ (8-Bit)	L	L	L		D <sub>OUT</sub>	Hi-Z	L/H
OUTPUT DISABLE	L	H	H		Hi-Z		*
			L		Hi-Z		*
STAND-BY	H	*	H		Hi-Z		*
			L		Hi-Z		*

\* : Don't Care

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Condition	Value	Unit
Operating temperature under bias	T <sub>opr</sub>	-	0 to 70	°C
Storage temperature	T <sub>stg</sub>	-	-55 to 125	°C
Input voltage	V <sub>I</sub>	relative to V <sub>SS</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Output voltage	V <sub>O</sub>		-0.5 to V <sub>CC</sub> + 0.5	V
Power supply voltage	V <sub>CC</sub>		-0.5 to 5	V
Power dissipation per package	P <sub>D</sub>		1.0	W

**RECOMMENDED OPERATING CONDITIONS FOR READ**

(Ta=0 to 70°C)						
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
V <sub>CC</sub> power supply voltage	V <sub>CC</sub>	V <sub>CC</sub> =3.0V-3.6V	3.0	-	3.6	V
Input "H" level	V <sub>IH</sub>		2.2	-	V <sub>CC</sub> +0.5*	V
Input "L" level	V <sub>IL</sub>		-0.5**	-	0.6	V

Voltage is relative to V<sub>SS</sub>\* : V<sub>CC</sub>+1.5V (Max.) when pulse width of overshoot is less than 10nS.

\*\* : -1.5V (Min.) when pulse width of undershoot is less than 10nS.

**ELECTRICAL CHARACTERISTICS (Read operation)****DC Characteristics**(V<sub>CC</sub>=3.3V±0.3V, Ta=0 to 70°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input leakage current	I <sub>LI</sub>	V <sub>I</sub> =0 to V <sub>CC</sub>	-	-	10	µA
Output leakage current	I <sub>LO</sub>	V <sub>O</sub> =0 to V <sub>CC</sub>	-	-	10	µA
V <sub>CC</sub> power supply current (Standby)	I <sub>CS1</sub>	CĒ=V <sub>CC</sub>	-	-	50	µA
	I <sub>CS2</sub>	CĒ=V <sub>IH</sub>	-	-	1	mA
V <sub>CC</sub> power supply current (Read)	I <sub>CCA</sub>	CĒ=V <sub>IL</sub> , OĒ=V <sub>IH</sub> tc=100ns	-	-	100	mA
Input "H" level	V <sub>IH</sub>	-	2.2	-	V <sub>CC</sub> +0.5*	V
Input "L" level	V <sub>IL</sub>	-	-0.5**	-	0.6	V
Output "H" level	V <sub>OH</sub>	I <sub>OH</sub> =-400µA	2.4	-	-	V
Output "L" level	V <sub>OL</sub>	I <sub>OL</sub> =2.1mA	-	-	0.4	V

Voltage is relative to V<sub>SS</sub>\*: V<sub>CC</sub>+1.5V (Max.) when pulse width of overshoot is less than 10nS.

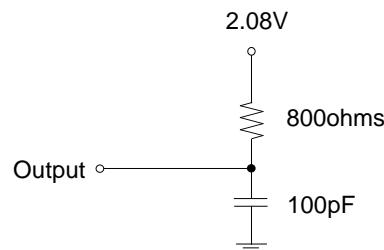
\*\*: -1.5V (Min.) when pulse width of undershoot is less than 10nS.

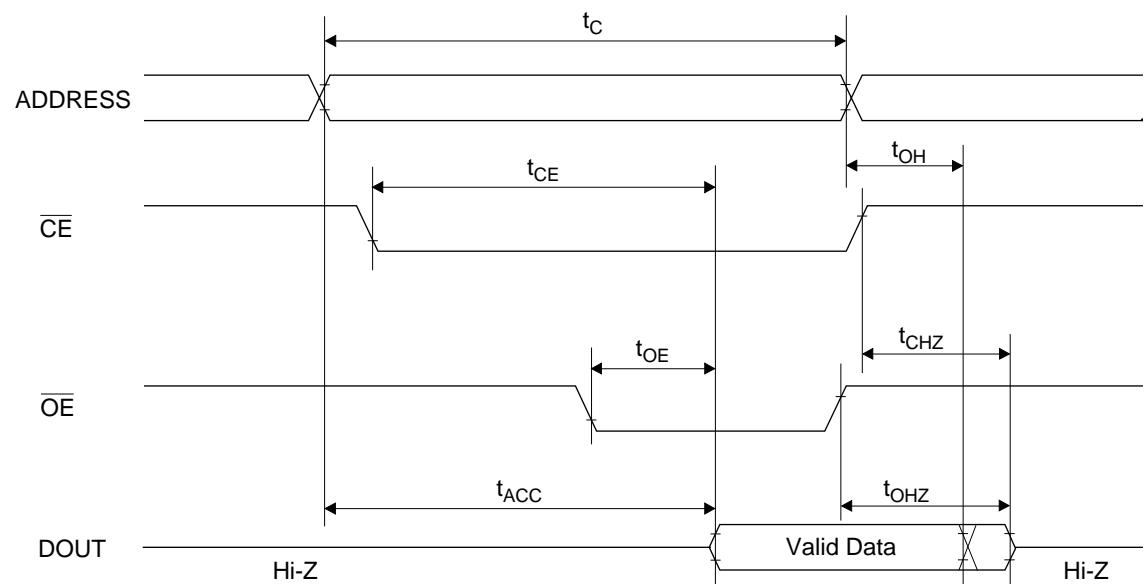
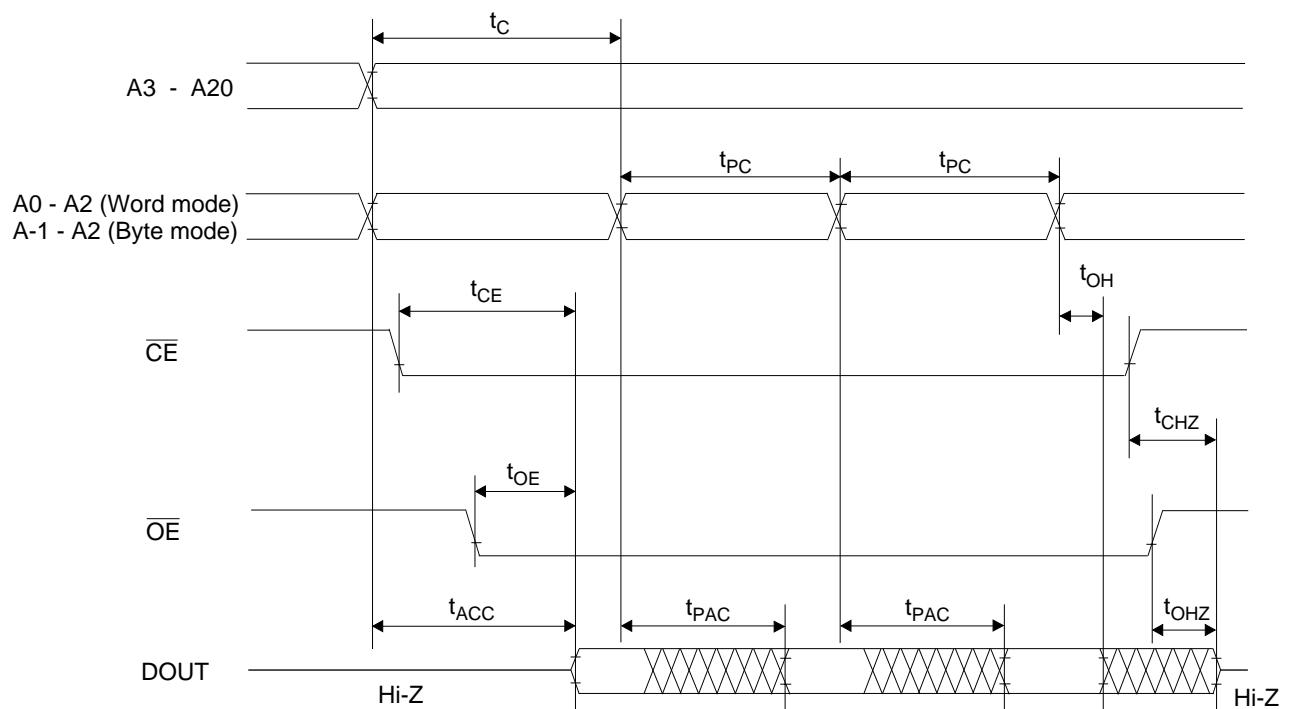
**AC Characteristics**(V<sub>CC</sub>=3.3V±0.3V, Ta=0 to 70°C)

Parameter	Symbol	Condition	Min.	Max.	Unit
Address access cycle time	T <sub>C</sub>	-	100	-	ns
Address access time	T <sub>ACC</sub>	CĒ=OĒ=V <sub>IL</sub>	-	100	ns
Page access cycle time	T <sub>PC</sub>	-	30	-	ns
Page access time	T <sub>PAC</sub>	-	-	30	ns
CĒ access time	T <sub>CE</sub>	OĒ=V <sub>IL</sub>	-	100	ns
OĒ access time	T <sub>OE</sub>	CĒ=V <sub>IL</sub>	-	40	ns
Output disable time	T <sub>CHZ</sub>	OĒ=V <sub>IL</sub>	0	30	ns
	T <sub>OHZ</sub>	CĒ=V <sub>IL</sub>	0	25	ns
Output hold time	T <sub>OH</sub>	CĒ=OĒ=V <sub>IL</sub>	0	-	ns

## Measurement conditions

- Input signal level ----- 0V/3V
- Input timing reference level ----- 0.8V/2.0V
- Output load ----- 100pF
- Output timing reference level ----- 0.8V/2.0V



**TIMING CHART****NORMAL MODE READ CYCLE****PAGE MODE READ CYCLE**

**PIN Capacitance**(V<sub>CC</sub>=3.3V, Ta=25°C, f=1MHz)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input	C <sub>IN1</sub>	V <sub>I</sub> =0V	-	-	8	pF
BYTE	C <sub>IN2</sub>		-	-	120	
Output	C <sub>OUT</sub>	V <sub>O</sub> =0V	-	-	10	